Low-power 2-input NAND gate Rev. 2 — 13 January 2022

### 1. General description

The 74AUP1G00-Q100 is a single 2-input NAND gate. Schmitt-trigger action at all inputs makes the circuit tolerant of slower input rise and fall times. This device ensures very low static and dynamic power consumption across the entire  $V_{CC}$  range from 0.8 V to 3.6 V. This device is fully specified for partial power down applications using  $I_{OFF}$ . The  $I_{OFF}$  circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

### 2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Wide supply voltage range from 0.8 V to 3.6 V
- CMOS low power dissipation
- High noise immunity
- Complies with JEDEC standards:
  - JESD8-12 (0.8 V to 1.3 V)
  - JESD8-11 (0.9 V to 1.65 V)
  - JESD8-7 (1.65 V to 1.95 V)
  - JESD8-5 (2.3 Vto 2.7 V)
  - JESD8C (2.7 V to 3.6 V)
- ESD protection:
  - HBM JESD22-A114F Class 3A exceeds 5000 V
  - MM JESD22-A115-A exceeds 200 V
  - MIL-STD-883, method 3015 Class 3A exceeds 5000 V
- Low static power consumption;  $I_{CC} = 0.9 \mu A$  (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Overvoltage tolerant inputs to 3.6 V
- Low noise overshoot and undershoot < 10 % of V<sub>CC</sub>
- I<sub>OFF</sub> circuitry provides partial Power-down mode operation

# nexperia

### 3. Ordering information

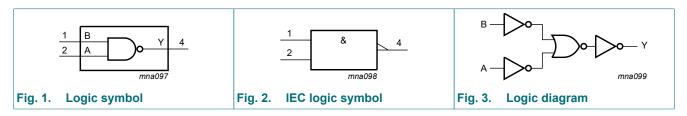
Table 1. Ordering information							
Type number	Package						
	Temperature range	Name	Description	Version			
74AUP1G00GW-Q100	-40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1			

### 4. Marking

Table 2. Marking			
Type number	Marking code [1]		
74AUP1G00GW-Q100	pA		

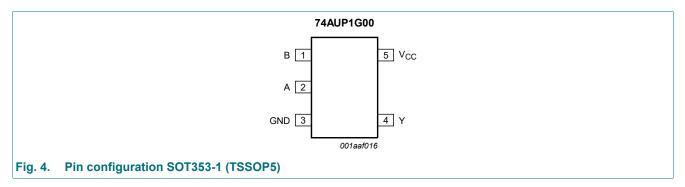
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

### 5. Functional diagram



### 6. Pinning information

### 6.1. Pinning



### 6.2. Pin description

Symbol	Pin	Description
В	1	data input
A	2	data input
GND	3	ground (0 V)
Y	4	data output
V <sub>cc</sub>	5	supply voltage

### 7. Functional description

#### Table 4. Function table

H = HIGH voltage level; L = LOW voltage level.

Input C		Output
Α	В	Y
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L

### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+4.6	V
I <sub>IK</sub>	input clamping current	V <sub>1</sub> < 0 V	-50	-	mA
VI	input voltage	[1]	-0.5	+4.6	V
I <sub>OK</sub>	output clamping current	V <sub>O</sub> < 0 V	-50	-	mA
Vo	output voltage	Active mode [1]	-0.5	V <sub>CC</sub> + 0.5	V
		Power-down mode; $V_{CC} = 0 V$ [1]	-0.5	+4.6	V
I <sub>O</sub>	output current	$V_{O} = 0 V$ to $V_{CC}$	-	±20	mA
I <sub>CC</sub>	supply current		-	+50	mA
I <sub>GND</sub>	ground current		-50	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = -40 °C to +125 °C [2]	-	250	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SOT353-1 (TSSOP5) package: Ptot derates linearly with 3.3 mW/K above 74 °C.

## 9. Recommended operating conditions

Table 6. I	Recommended operating conditions				
Symbol	Parameter	Conditions	Min	Мах	Unit
V <sub>CC</sub>	supply voltage		0.8	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode	0	V <sub>CC</sub>	V
		Power-down mode; V <sub>CC</sub> = 0 V	0	3.6	V
T <sub>amb</sub>	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	$V_{CC} = 0.8 V \text{ to } 3.6 V$	0	200	ns/V

### **10. Static characteristics**

#### Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
T <sub>amb</sub> = 2	25 °C		<b>I</b>			_
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 0.8 V	0.70×V <sub>CC</sub>	-	-	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	0.65×V <sub>CC</sub>	-	-	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.6	-	-	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.0	-	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 0.8 V	-	-	0.30×V <sub>CC</sub>	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	-	-	0.35×V <sub>CC</sub>	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	0.7	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	-	0.9	V
V <sub>OH</sub>	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_{O}$ = -20 µA; $V_{CC}$ = 0.8 V to 3.6 V	V <sub>CC</sub> - 0.1	-	-	V
		I <sub>O</sub> = -1.1 mA; V <sub>CC</sub> = 1.1 V	0.75×V <sub>CC</sub>	-	-	V
		I <sub>O</sub> = -1.7 mA; V <sub>CC</sub> = 1.4 V	1.11	-	-	V
		I <sub>O</sub> = -1.9 mA; V <sub>CC</sub> = 1.65 V	1.32	-	-	V
		I <sub>O</sub> = -2.3 mA; V <sub>CC</sub> = 2.3 V	2.05	-	-	V
		I <sub>O</sub> = -3.1 mA; V <sub>CC</sub> = 2.3 V	1.9	-	-	V
		I <sub>O</sub> = -2.7 mA; V <sub>CC</sub> = 3.0 V	2.72	-	-	V
		I <sub>O</sub> = -4.0 mA; V <sub>CC</sub> = 3.0 V	2.6	-	-	V
V <sub>OL</sub>	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_{O}$ = 20 µA; $V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	0.3×V <sub>CC</sub>	V
		I <sub>O</sub> = 1.7 mA; V <sub>CC</sub> = 1.4 V	-	-	0.31	V
		I <sub>O</sub> = 1.9 mA; V <sub>CC</sub> = 1.65 V	-	-	0.31	V
		I <sub>O</sub> = 2.3 mA; V <sub>CC</sub> = 2.3 V		-	0.31	V
		I <sub>O</sub> = 3.1 mA; V <sub>CC</sub> = 2.3 V	-	-	0.44	V
		I <sub>O</sub> = 2.7 mA; V <sub>CC</sub> = 3.0 V	-	-	0.31	V
		I <sub>O</sub> = 4.0 mA; V <sub>CC</sub> = 3.0 V	-	-	0.44	V

### Low-power 2-input NAND gate

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
l <sub>l</sub>	input leakage current	$V_1$ = GND to 3.6 V; $V_{CC}$ = 0 V to 3.6 V	-	-	±0.1	μA
I <sub>OFF</sub>	power-off leakage current	$V_1$ or $V_0$ = 0 V to 3.6 V; $V_{CC}$ = 0 V	-	-	±0.2	μA
ΔI <sub>OFF</sub>	additional power-off leakage current	$V_{I} \text{ or } V_{O} = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.2	μA
I <sub>CC</sub>	supply current	$V_I$ = GND or $V_{CC}$ ; $I_O$ = 0 A; $V_{CC}$ = 0.8 V to 3.6 V	-	-	0.5	μA
$\Delta I_{CC}$	additional supply current	$V_1 = V_{CC} - 0.6 V; I_O = 0 A; V_{CC} = 3.3 V$ [1]	-	-	40	μA
CI	input capacitance	$V_{CC}$ = 0 V to 3.6 V; V <sub>I</sub> = GND or V <sub>CC</sub>	-	0.8	-	pF
Co	output capacitance	$V_{O} = GND; V_{CC} = 0 V$	-	1.7	-	pF
T <sub>amb</sub> = -4	40 °C to +85 °C					-
VIH	HIGH-level input voltage	V <sub>CC</sub> = 0.8 V	0.70×V <sub>CC</sub>	-	-	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.6	-	-	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.0	-	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 0.8 V	-	-	0.30×V <sub>CC</sub>	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	-	-	0.35×V <sub>CC</sub>	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	0.7	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	-	0.9	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		$I_{O}$ = -20 µA; $V_{CC}$ = 0.8 V to 3.6 V	V <sub>CC</sub> - 0.1	-	-	V
		I <sub>O</sub> = -1.1 mA; V <sub>CC</sub> = 1.1 V	0.7×V <sub>CC</sub>	-	-	V
		I <sub>O</sub> = -1.7 mA; V <sub>CC</sub> = 1.4 V	1.03	-	-	V
		I <sub>O</sub> = -1.9 mA; V <sub>CC</sub> = 1.65 V	1.30	-	-	V
		I <sub>O</sub> = -2.3 mA; V <sub>CC</sub> = 2.3 V	1.97	-	-	V
		I <sub>O</sub> = -3.1 mA; V <sub>CC</sub> = 2.3 V	1.85	-	-	V
		I <sub>O</sub> = -2.7 mA; V <sub>CC</sub> = 3.0 V	2.67	-	-	V
		I <sub>O</sub> = -4.0 mA; V <sub>CC</sub> = 3.0 V	2.55	-	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		$I_{O}$ = 20 µA; $V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	0.3×V <sub>CC</sub>	V
		I <sub>O</sub> = 1.7 mA; V <sub>CC</sub> = 1.4 V	-	-	0.37	V
		I <sub>O</sub> = 1.9 mA; V <sub>CC</sub> = 1.65 V	-	-	0.35	V
		I <sub>O</sub> = 2.3 mA; V <sub>CC</sub> = 2.3 V	-	-	0.33	V
		I <sub>O</sub> = 3.1 mA; V <sub>CC</sub> = 2.3 V	-	-	0.45	V
		I <sub>O</sub> = 2.7 mA; V <sub>CC</sub> = 3.0 V	-	-	0.33	V
		I <sub>O</sub> = 4.0 mA; V <sub>CC</sub> = 3.0 V	-	-	0.45	V
I <sub>I</sub>	input leakage current	V <sub>1</sub> = GND to 3.6 V; V <sub>CC</sub> = 0 V to 3.6 V	-	-	±0.5	μA
I <sub>OFF</sub>	power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V}; V_{CC} = 0 \text{ V}$	-	-	±0.5	μA
Δl <sub>OFF</sub>	additional power-off leakage current	$V_{I} \text{ or } V_{O} = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.6	μA
I <sub>CC</sub>	supply current	$V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.9	μA
Δl <sub>CC</sub>	additional supply current	$V_1 = V_{CC} - 0.6 V; I_0 = 0 A; V_{CC} = 3.3 V$ [1]	-	-	50	μA

### Low-power 2-input NAND gate

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
T <sub>amb</sub> = -4	40 °C to +125 °C		1			
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 0.8 V	0.75×V <sub>CC</sub>	-	-	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	0.70×V <sub>CC</sub>	-	-	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.6	-	-	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.0	-	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 0.8 V	-	-	0.25×V <sub>CC</sub>	V
		V <sub>CC</sub> = 0.9 V to 1.95 V	-	-	0.30×V <sub>CC</sub>	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	0.7	V
		V <sub>CC</sub> = 3.0 V to 3.6 V	-	-	0.9	V
V <sub>OH</sub>	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_{O}$ = -20 µA; $V_{CC}$ = 0.8 V to 3.6 V	V <sub>CC</sub> - 0.11	-	-	V
		I <sub>O</sub> = -1.1 mA; V <sub>CC</sub> = 1.1 V	0.6×V <sub>CC</sub>	-	-	V
		I <sub>O</sub> = -1.7 mA; V <sub>CC</sub> = 1.4 V	0.93	-	-	V
		I <sub>O</sub> = -1.9 mA; V <sub>CC</sub> = 1.65 V	1.17	-	-	V
		I <sub>O</sub> = -2.3 mA; V <sub>CC</sub> = 2.3 V	1.77	-	-	V
		I <sub>O</sub> = -3.1 mA; V <sub>CC</sub> = 2.3 V	1.67	-	-	V
		I <sub>O</sub> = -2.7 mA; V <sub>CC</sub> = 3.0 V	2.40	-	-	V
		I <sub>O</sub> = -4.0 mA; V <sub>CC</sub> = 3.0 V	2.30	-	-	V
V <sub>OL</sub>	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_{O}$ = 20 µA; $V_{CC}$ = 0.8 V to 3.6 V	-	-	0.11	V
		I <sub>O</sub> = 1.1 mA; V <sub>CC</sub> = 1.1 V	-	-	0.33×V <sub>CC</sub>	V
		I <sub>O</sub> = 1.7 mA; V <sub>CC</sub> = 1.4 V	-	-	0.41	V
		I <sub>O</sub> = 1.9 mA; V <sub>CC</sub> = 1.65 V	-	-	0.39	V
		I <sub>O</sub> = 2.3 mA; V <sub>CC</sub> = 2.3 V	-	-	0.36	V
		I <sub>O</sub> = 3.1 mA; V <sub>CC</sub> = 2.3 V	-	-	0.50	V
		I <sub>O</sub> = 2.7 mA; V <sub>CC</sub> = 3.0 V	-	-	0.36	V
		I <sub>O</sub> = 4.0 mA; V <sub>CC</sub> = 3.0 V	-	-	0.50	V
I <sub>I</sub>	input leakage current	$V_{I}$ = GND to 3.6 V; $V_{CC}$ = 0 V to 3.6 V	-	-	±0.75	μA
I <sub>OFF</sub>	power-off leakage current	$V_1$ or $V_0$ = 0 V to 3.6 V; $V_{CC}$ = 0 V	-	-	±0.75	μA
ΔI <sub>OFF</sub>	additional power-off leakage current	$V_{I} \text{ or } V_{O} = 0 \text{ V to } 3.6 \text{ V;}$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.75	μA
I <sub>CC</sub>	supply current	$V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	1.4	μA
ΔI <sub>CC</sub>	additional supply current	$V_1 = V_{CC} - 0.6 V; I_0 = 0 A; V_{CC} = 3.3 V$ [1]	-	-	75	μA

[1] One input at  $V_{CC}$  - 0.6 V, other input at  $V_{CC}$  or GND.

# **11. Dynamic characteristics**

#### Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Fig. 6

Symbol	Parameter	Conditions		Min	Тур [1]	Мах	Unit
T <sub>amb</sub> = 2	25 °C; C <sub>L</sub> = 5 pF						
t <sub>pd</sub>	propagation delay	A, B to Y; see <u>Fig. 5</u>	[2]				
		V <sub>CC</sub> = 0.8 V		-	17.5	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V		2.5	5.3	11.0	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V		2.0	3.8	6.8	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V		1.6	3.1	5.3	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V		1.3	2.5	4.0	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V		1.0	2.2	3.6	ns
T <sub>amb</sub> = 2	25 °C; C <sub>L</sub> = 10 pF						
t <sub>pd</sub>	propagation delay	A, B to Y; see <u>Fig. 5</u>	[2]				
		V <sub>CC</sub> = 0.8 V		-	21.0	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V		2.4	6.1	13.0	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V		2.4	4.4	7.9	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V		2.0	3.7	6.2	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V		1.4	3.0	4.7	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V		1.3	2.8	4.3	ns
T <sub>amb</sub> = 2	25 °C; C <sub>L</sub> = 15 pF		I				
t <sub>pd</sub>	propagation delay	A, B to Y; see Fig. 5	[2]				
		V <sub>CC</sub> = 0.8 V		-	24.5	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V		3.4	6.9	14.8	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V		2.8	5.0	8.9	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V		2.0	4.1	7.0	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V		1.7	3.5	5.3	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V		1.6	3.2	4.9	ns
T <sub>amb</sub> = 2	25 °C; C <sub>L</sub> = 30 pF						
t <sub>pd</sub>	propagation delay	A, B to Y; see Fig. 5	[2]				
		V <sub>CC</sub> = 0.8 V		-	34.8	-	ns
		V <sub>CC</sub> = 1.1 V to 1.3 V		4.6	9.2	20.1	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V		3.0	6.5	11.8	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V		2.6	5.4	9.3	ns
		$V_{CC}$ = 2.3 V to 2.7 V		2.4	4.6	7.1	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V		2.3	4.3	6.5	ns

#### Low-power 2-input NAND gate

Symbol	Parameter	Conditions	Min	Тур [1]	Max	Unit
T <sub>amb</sub> = 2	5 °C					
C <sub>PD</sub>	power dissipation	$f = 1 \text{ MHz}; V_I = \text{GND to } V_{CC}$ [3	]			
	capacitance	V <sub>CC</sub> = 0.8 V	-	2.6	-	pF
		V <sub>CC</sub> = 1.1 V to 1.3 V	-	2.8	-	pF
		V <sub>CC</sub> = 1.4 V to 1.6 V	-	2.9	-	pF
		V <sub>CC</sub> = 1.65 V to 1.95 V	-	3.1	-	pF
		$V_{CC}$ = 2.3 V to 2.7 V	-	3.6	-	pF
		$V_{CC}$ = 3.0 V to 3.6 V	-	4.2	-	pF

All typical values are measured at nominal V<sub>CC</sub>. [1]

[2] [3] f<sub>o</sub> = output frequency in MHz;  $C_L$  = output load capacitance in pF; V<sub>CC</sub> = supply voltage in V;

N = number of inputs switching;  $\Sigma(C_L \times V_{CC}^2 \times f_o)$  = sum of the outputs.

#### Table 9. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Fig. 6

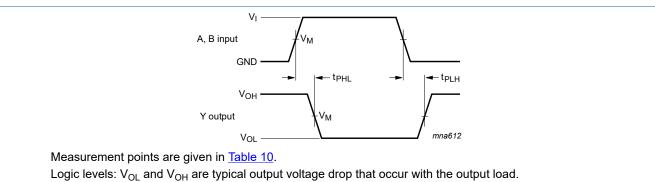
Symbol	Parameter	Conditions		-40 °C t	o +85 °C	-40 °C to	o +125 °C	Unit
				Min	Max	Min	Max	
C <sub>L</sub> = 5 p	F					1		
t <sub>pd</sub>	propagation delay	A, B to Y; see Fig. 5	[1]					
		V <sub>CC</sub> = 1.1 V to 1.3 V		2.1	12.2	2.1	13.5	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V		1.8	7.8	1.8	8.6	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V		1.4	6.2	1.4	6.9	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V		1.1	4.7	1.1	5.2	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V		1.0	4.2	1.0	4.7	ns
C <sub>L</sub> = 10	pF	· ·	·					
t <sub>pd</sub>	propagation delay	A, B to Y; see Fig. 5	[1]					
		V <sub>CC</sub> = 1.1 V to 1.3 V		2.2	14.4	2.2	15.9	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V		2.2	9.2	2.2	10.2	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V		1.9	7.3	1.9	8.1	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V		1.3	5.6	1.3	6.2	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V		1.2	4.9	1.2	5.4	ns
C <sub>L</sub> = 15	pF	·	·					
t <sub>pd</sub>	propagation delay	A, B to Y; see Fig. 5	[1]					
		V <sub>CC</sub> = 1.1 V to 1.3 V		3.1	16.5	3.1	18.2	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V		2.5	10.5	2.5	11.6	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V		2.0	8.3	2.0	9.2	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V		1.5	6.4	1.5	7.1	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V		1.4	5.7	1.4	6.3	ns

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Symbol	Parameter	Conditions	-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Max	Min	Max	1
C <sub>L</sub> = 30	pF						
t <sub>pd</sub>	propagation delay	A, B to Y; see <u>Fig. 5</u> [1]					
		V <sub>CC</sub> = 1.1 V to 1.3 V	4.1	22.6	4.1	24.9	ns
		V <sub>CC</sub> = 1.4 V to 1.6 V	2.9	14.0	2.9	15.4	ns
		V <sub>CC</sub> = 1.65 V to 1.95 V	2.3	11.1	2.3	12.3	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	2.1	8.5	2.1	9.4	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	2.1	7.6	2.1	8.4	ns

[1]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .

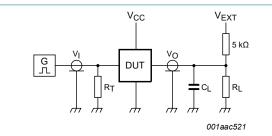
### 11.1. Waveforms and test circuit



#### Fig. 5. The data input (A or B) to output (Y) propagation delays

#### Table 10. Measurement points

Supply voltage	Input	Output		
V <sub>cc</sub>	V <sub>M</sub>	VI	t <sub>r</sub> = t <sub>f</sub>	V <sub>M</sub>
0.8 V to 3.6 V	0.5 × V <sub>CC</sub>	V <sub>CC</sub>	≤ 3.0 ns	0.5 × V <sub>CC</sub>



Test data is given in Table 11.

Definitions for test circuit:

R<sub>L</sub> = Load resistance;

C<sub>L</sub> = Load capacitance including jig and probe capacitance;

 $R_T$  = Termination resistance should be equal to the output impedance  $Z_0$  of the pulse generator;

V<sub>EXT</sub> = External voltage for measuring switching times.

#### Test circuit for measuring switching times Fig. 6.

### Low-power 2-input NAND gate

Table 11. Test data

Supply voltage	Load		V <sub>EXT</sub>		
V <sub>cc</sub>	CL	R <sub>L</sub> [1]	t <sub>PLH</sub> , t <sub>PHL</sub>	t <sub>PZH</sub> , t <sub>PHZ</sub>	t <sub>PZL</sub> , t <sub>PLZ</sub>
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 kΩ or 1 MΩ	open	GND	2 × V <sub>CC</sub>

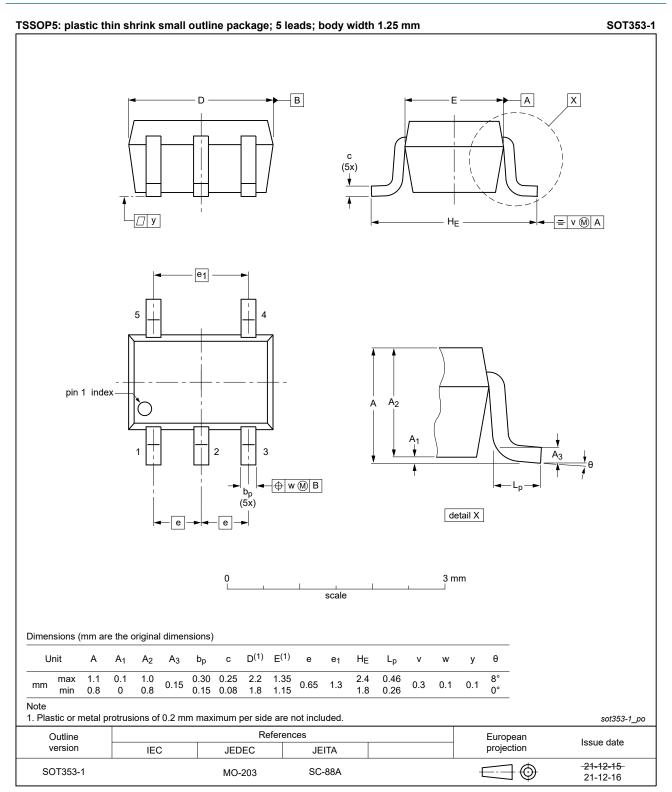
[1] For measuring enable and disable times  $R_L = 5 k\Omega$ .

For measuring propagation delays, setup and hold times and pulse width  $R_L$  = 1 M $\Omega$ .

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### 12. Package outline



#### Fig. 7. Package outline SOT353-1 (TSSOP5)

74AUP1G00\_Q100

### 13. Abbreviations

Acronym	Description
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MIL	Military
MM	Machine Model

### 14. Revision history

#### Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
74AUP1G00_Q100 v.2	20220113	Product data sheet	-	74AUP1G00_Q100 v.1	
Modifications:	<ul> <li><u>Section 1</u> and <u>Section 2</u> updated.</li> <li><u>Table 5</u>: Derating values for P<sub>tot</sub> total power dissipation updated.</li> <li><u>Fig. 7</u>: Package outline drawing for SOT353-1 (TSSOP5) has changed.</li> </ul>				
74AUP1G00_Q100 v.1	20190404	Product data sheet	-	-	

### 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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